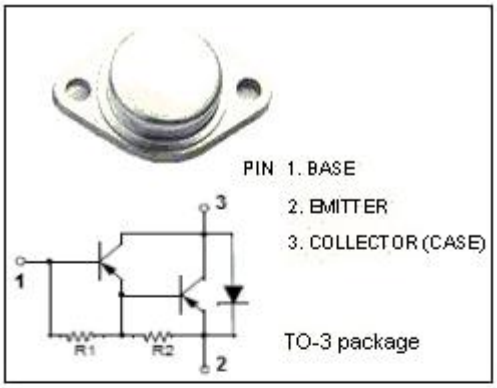
isc Silicon PNP Darlington Power Transistor — 2SA1046

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= -100V(Min)
- High Current Capability
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

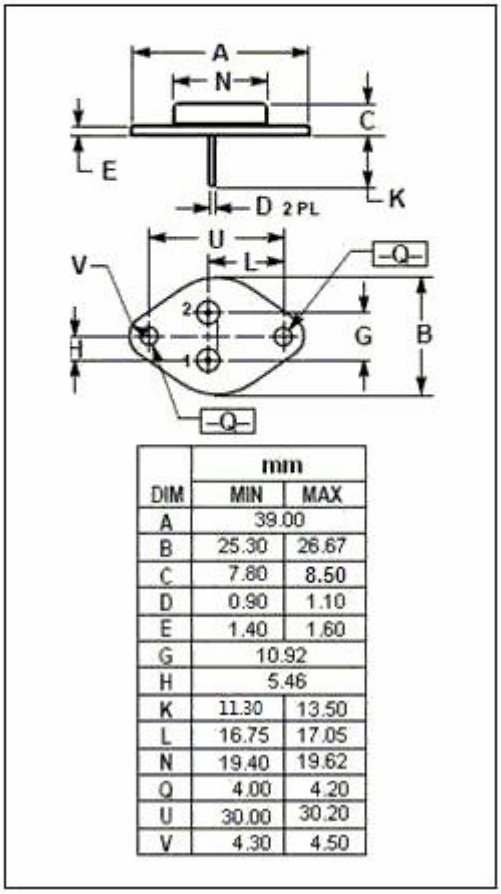


APPLICATIONS

- Power switching applications
- High frequency power amplifier
- DC-DC converters

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @ T_C=25℃	100	W
T_J	Junction Temperature	175	℃
T_{stg}	Storage Temperature Range	-65~175	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; R_{BE}= ∞	-100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -50 μ A; I_E= 0	-100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -2mA ; I_C= 0	-5			V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V ; I_E= 0			-50	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-50	μ A
h_{FE}	DC Current Gain	I_C= -3A ; V_{CE}= -3V		3000		